





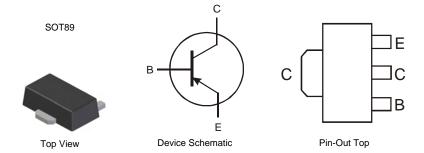
40V LOW V_{CE(sat)} PNP SURFACE MOUNT TRANSISTOR

Features

- Ultra Low Collector-Emitter Saturation Voltage
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Weight: 0.055 grams (approximate)



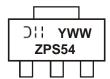
Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS5540X-13	ZPS54	13	12mm	2,500

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com
- 3. For packaging details, please go to our website at http://www.diodes.com

Marking Information



ZPS54 = Product Type Marking Code

| | = Manufacturer's Code Marking

YWW = Date Code Marking

Y = Last digit of year (ex: 8 = 2008)

WW = Week code (01 - 53)



Maximum Ratings @TA = 25°C unless otherwise specified

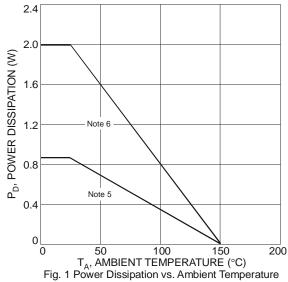
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-6	V
Peak Pulse Collector Current	I _{CM}	-10	А
Repetitive Peak Pulse Collector Current (Note 4)	I _{CRP}	-5	Α
Continuous Collector Current	I _C	-4	А
Peak Pulse Base Current	I _{BM}	-2	Α
Continuous Base Current	I _B	-1	A

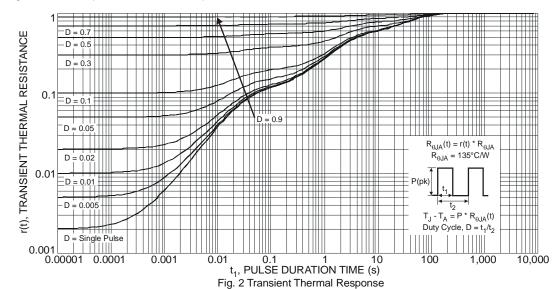
Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) @ T _A = 25°C	P _D	0.9	W
Thermal Resistance, Junction to Ambient Air (Note 5) @ T _A = 25°C	$R_{ heta JA}$	139	°C/W
Power Dissipation (Note 6) @ T _A = 25°C	P _D	2	W
Thermal Resistance, Junction to Ambient Air (Note 6) @ T _A = 25°C	$R_{ heta JA}$	62.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 4. Pulse width ≤ 10ms; Duty cycle ≤ 0.2
 5. Device mounted on FR-4 PCB with minimum recommended pad layout.
 6. Device mounted on FR-4 PCB with 1inch² copper pad layout.



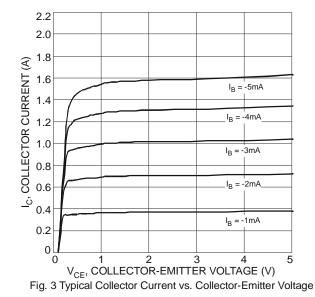


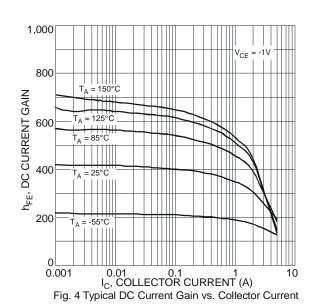


Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions	
Collector-Base Breakdown Voltage	BV _{CBO}	-40	_	_	V	$I_C = -100 \mu A$	
Collector-Emitter Breakdown Voltage (Note 7)	BV _{CEO}	-40	_	_	V	$I_C = -10 \text{mA}$	
Emitter-Base Breakdown Voltage	BV _{EBO}	-6	_	_	V	$I_E = -100 \mu A$	
Collector-Base Cutoff Current	I _{CBO}			-100	nA	$V_{CB} = -30V, I_{E} = 0$	
Collector-Base Cuton Current				-50	μΑ	$V_{CB} = -30V$, $I_E = 0$, $T_A = 150$ °C	
Emitter-Base Cutoff Current	I _{EBO}			-100	nA	$V_{EB} = -5V, I_C = 0$	
		250		_		$V_{CE} = -2V, I_{C} = -0.5A$	
DC Current Gain (Note 6)	h	200	350	_		$V_{CE} = -2V, I_{C} = -1A$	
DC Current Gain (Note 6)	h _{FE}	150			_	$V_{CE} = -2V, I_{C} = -2A$	
		50	_	_		$V_{CE} = -2V, I_{C} = -5A$	
		_	_	-120		$I_C = -0.5A$, $I_B = -5mA$	
	V _{CE(sat)}			-170	mV	$I_C = -1A$, $I_B = -10mA$	
Collector-Emitter Saturation Voltage (Note 7)			-70	-160		$I_C = -2A$, $I_B = -200mA$	
			-165	-340		$I_C = -4A$, $I_B = -200mA$	
			-150	-375		$I_C = -5A$, $I_B = -500mA$	
Equivalent On-Resistance	R _{CE(sat)}		-30	-75	mΩ	$I_C = -5A$, $I_B = -500mA$	
Base-Emitter Saturation Voltage	V _{BE(sat)}			-1.1	V	$I_C = -4A$, $I_B = -200mA$	
base-Emilier Saluration Voltage				-1.2		$I_C = -5A$, $I_B = -500mA$	
Base-Emitter Turn-on Voltage	V _{BE(on)}			-1.0	V	$V_{CE} = -2V, I_{C} = -2A$	
Transition Frequency	f _T	60			MHz	$V_{CE} = -10V$, $I_{C} = -0.1A$, $f = 100MHz$	
Collector Capacitance	C _c			105	рF	$V_{CB} = -10V$, $I_E = 0A$, $f = 1MHz$	
Turn-On Time	ton		63		ns		
Delay Time	t _d		15		ns		
Rise Time	t _r	_	48	_	ns	$V_{CC} = -10V, I_C = -2A,$	
Turn-Off Time	t _{off}		280		ns	$I_{B1} = -I_{B2} = -200 \text{mA}$	
Storage Time	ts		232	_	ns		
Fall Time	t _f	_	48	_	ns		

Notes: 7. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.







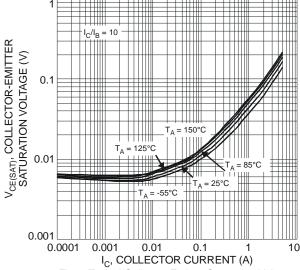
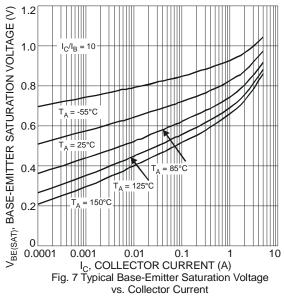
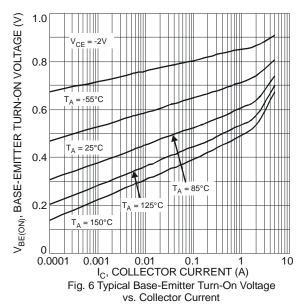
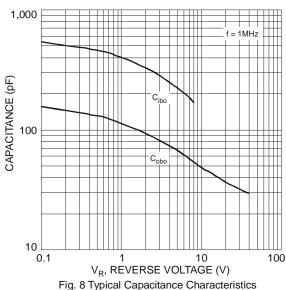


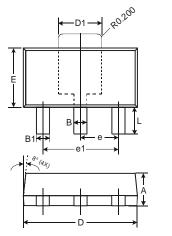
Fig. 5 Typical Collector-Emitter Saturation Voltage vs. Collector Current

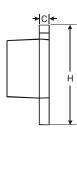






Package Outline Dimensions

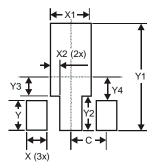




SO 189				
Dim	Min	Max		
Α	1.40	1.60		
В	0.44	0.62		
B1	0.35	0.54		
С	0.35	0.43		
D	4.40	4.60		
D1	1.52	1.83		
Е	2.29	2.60		
е	1.50 Typ			
e1	3.00 Typ			
Η	3.94	4.25		
L	0.89	1.20		
All Dimensions in mm				



Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.900
X1	1.733
X2	0.416
Υ	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
С	1.500

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